

*D1005

*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET

*May 2004

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*          _____GATE
*          I  _____DRAIN
*          I  I  _____SOURCE
*          I  I  I
.SUBCKT D1005  10  20  30
*Cin1,Cin2 & Lin model the input side of the package
Cin1  10  30  0.45p
Lin   10  11  0.68n
Cin2  11  30  0.45p
LG    11  12  0.3n   ;Gate bond wire inductance
CGS   12  13  184p   ;Gate-source capacitance
MOS   14  12  13    13  D1005 L=0.9U W=0.224   ;D G S B LEVEL1
JFET  16  13  14    D1005                       ;D G S
DBODY 13  16  D1005                               ;P N
LS    13  30  0.6n   ;Source bond wire inductance
CGD   12  16  4p     ;Gate-drain feedback capacitance

*Cout1,Cout2 & Lout model the output side of the package
Cout1  16  30  1.2p
Lout   16  20  1.68n
Cout2  20  30  1.2p

.MODEL D1005  NMOS (VTO=4.76 KP=2.811E-5 LAMBDA=0.032 RD=0.019 RS=0.077)
.MODEL D1005  NJF  (VTO=-4.3 BETA=1 LAMBDA=0.54)
.MODEL D1005  D    (CJO=328.8P RS=0.25 VJ=0.7 M=0.35 BV=75)

.ENDS
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